View Online at https://aerobasegroup.com/nsn/5961-01-105-4621

Inclosure Material:

Ceramic all transistor

Overall Length:

0.980 inches all transistor

Overall Height:

0.300 inches all transistor

Overall Width:

0.850 inches all transistor

Mounting Facility Quantity:

2 all transistor

Internal Configuration:

Junction contact all transistor

Internal Junction Configuration:

Npn all transistor

Component Function Relationship:

Matched

Component Name And Quantity:

4 transistor

Mounting Method:

Unthreaded hole all transistor

Field Force Effect Type:

Electrostatic charge

Semiconductor Material:

Silicon all transistor

Voltage Rating In Volts Per Characteristic:

65.0 collector to base voltage/static/emitter open all transistor and 33.0 collector to emitter voltage/static/base open all transistor and 65.0 collector to emitter voltage, dc with base short-circuited to emitter all transistor and 4.0 emitter to base voltage, static, collector open all transistor

Current Rating Per Characteristic:

3.00 amperes source cutoff current all transistor and 20.00 amperes source cutoff current all transistor

Power Rating Per Characteristic:

270.0 watts small-signal input power, common-collector absolute all transistor

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius junction all transistor

Special Features:

Case contains beryllium oxide - handle and dispose iaw hazmat procedures

Test Data Document:

13499-352-1108 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

6 ribbon all transistor

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

No

Fiig:

A110a0